



N-Channel 250-V (D-S) 175°C MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
250	0.165 @ $V_{GS} = 10$ V	18

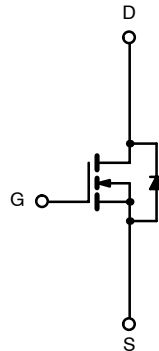
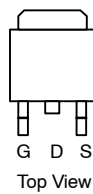
FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- New Low Thermal Resistance Package

APPLICATIONS

- Automotive Such As:
 - Diesel Fuel Injection
 - High-Side Switch
 - Motor Drives

TO-263



Ordering Information: SUM18N25-165—E3 (Lead Free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	250	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	18
		$T_C = 125^\circ\text{C}$	10.4
Pulsed Drain Current	I_{DM}	20	A
Single Pulse Avalanche Current	I_{AS}	5	
Single Pulse Avalanche Energy ^a	E_{AS}	1.25	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	3.75
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	$^\circ\text{C/W}$
Junction-to-Case (Drain)	R_{thJC}	1.0	

Notes

- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

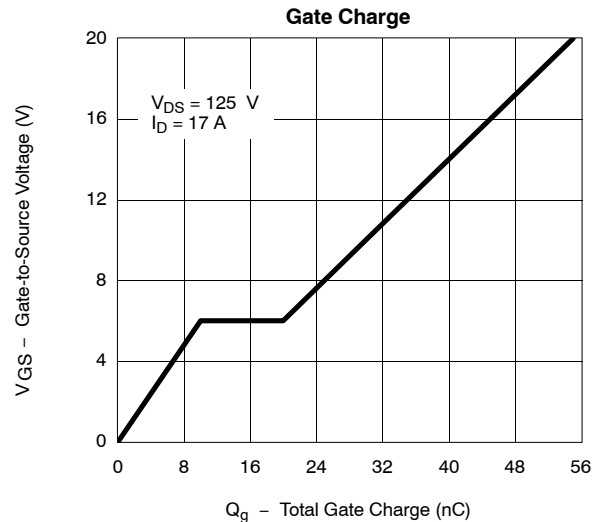
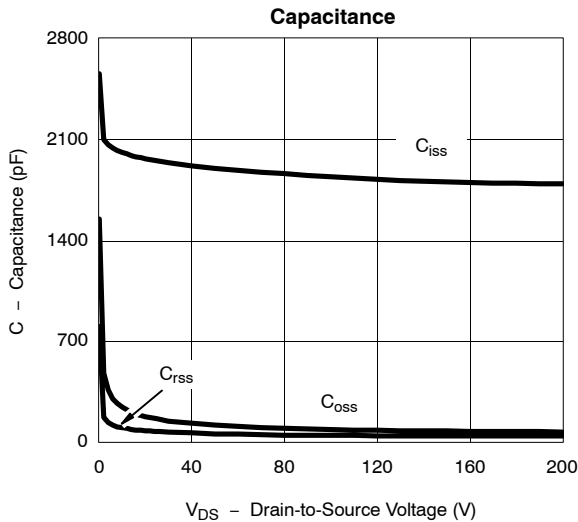
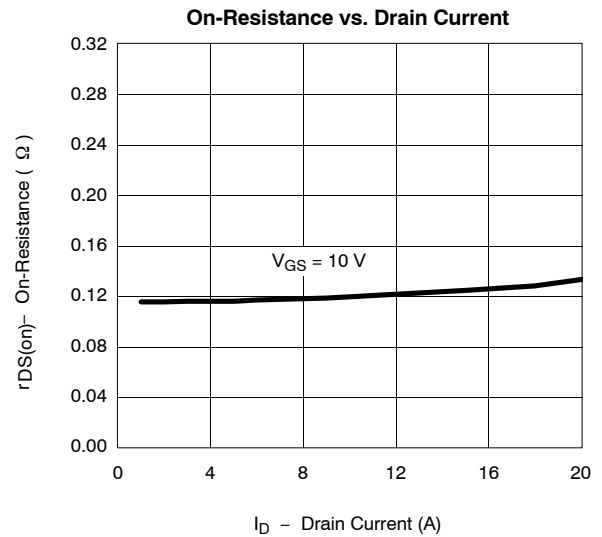
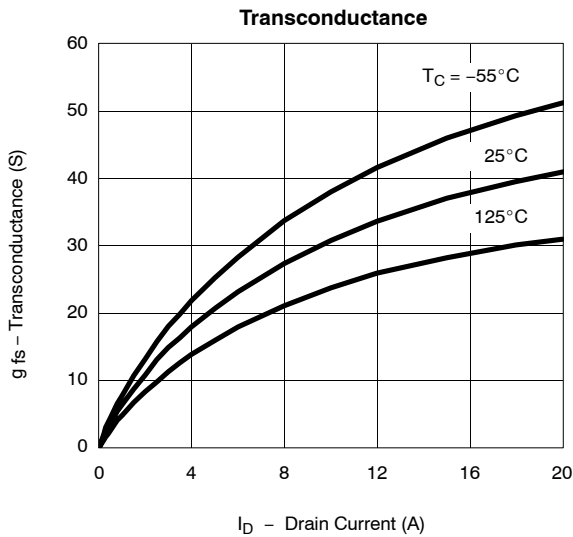
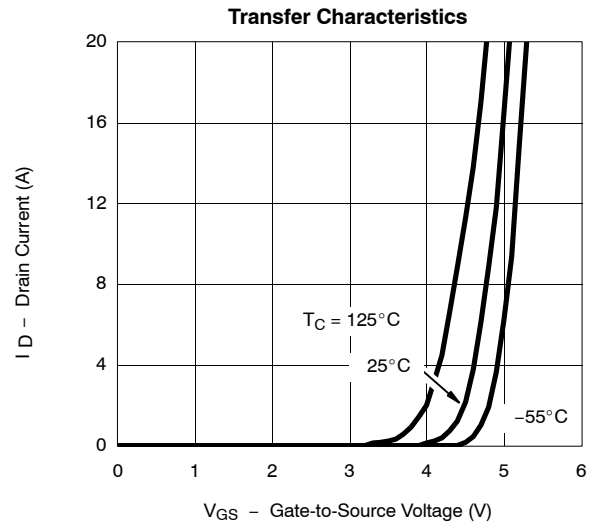
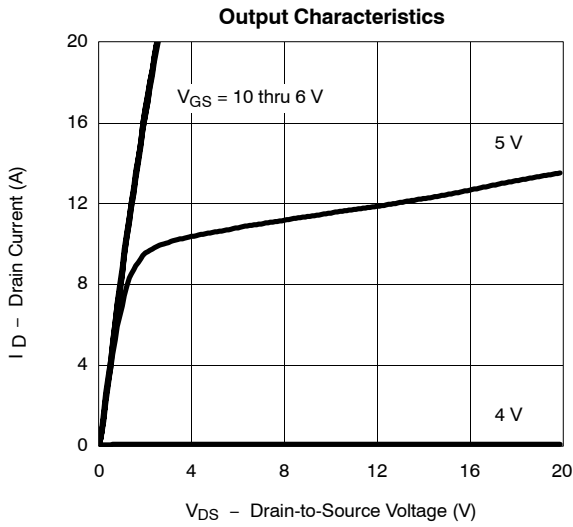
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	250			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V			1	μA
		V _{DS} = 250 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 250 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 15 V, V _{GS} = 10 V	20			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 14 A		0.130	0.165	Ω
		V _{GS} = 10 V, I _D = 14 A, T _J = 125 °C			0.347	
		V _{GS} = 10 V, I _D = 14 A, T _J = 175 °C			0.462	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 18 A		36		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		1950		pF
Output Capacitance	C _{oss}			160		
Reverse Transfer Capacitance	C _{rss}			70		
Total Gate Charge ^c	Q _g	V _{DS} = 125 V, V _{GS} = 10 V, I _D = 18 A		30	45	nC
Gate-Source Charge ^c	Q _{gs}			10		
Gate-Drain Charge ^c	Q _{gd}			10		
Gate Resistance	R _g			1.6		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 125 V, R _L = 7.0 Ω I _D ≅ 18 A, V _{GEN} = 10 V, R _g = 2.5 Ω		15	25	ns
Rise Time ^c	t _r			130	195	
Turn-Off Delay Time ^c	t _{d(off)}			30	45	
Fall Time ^c	t _f			100	150	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _S				18	A
Pulsed Current	I _{SM}				20	
Forward Voltage ^a	V _{SD}	I _F = 18 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 18 A, di/dt = 100 A/μs		115	175	ns
Peak Reverse Recovery Current	I _{RM(REC)}			10	15	A
Reverse Recovery Charge	Q _{rr}			0.58	1.3	μC

Notes

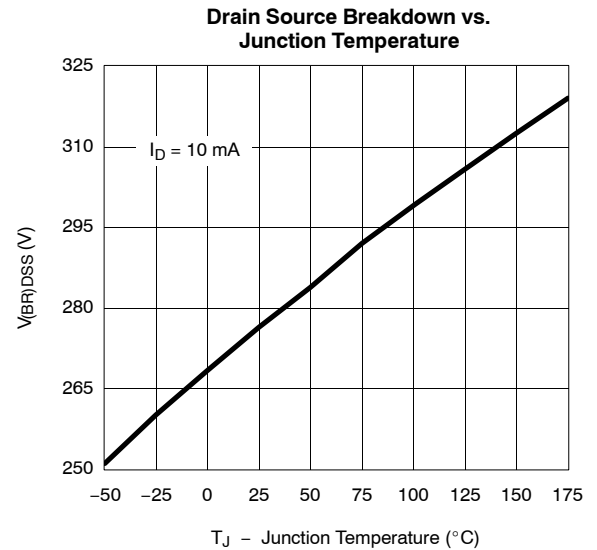
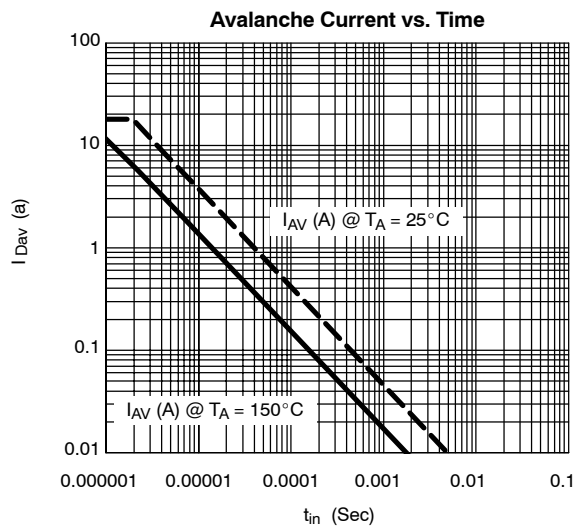
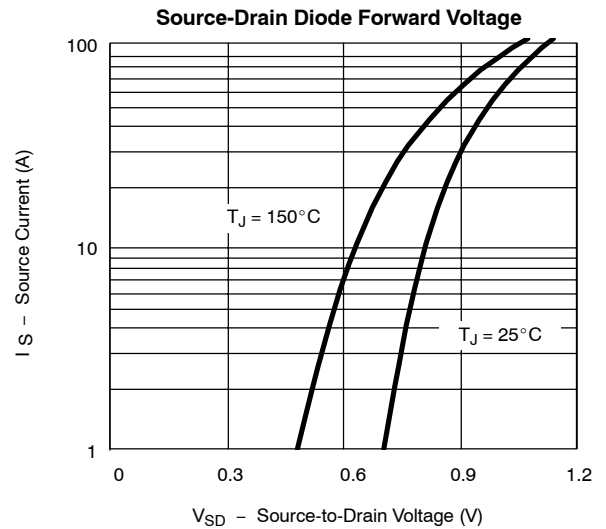
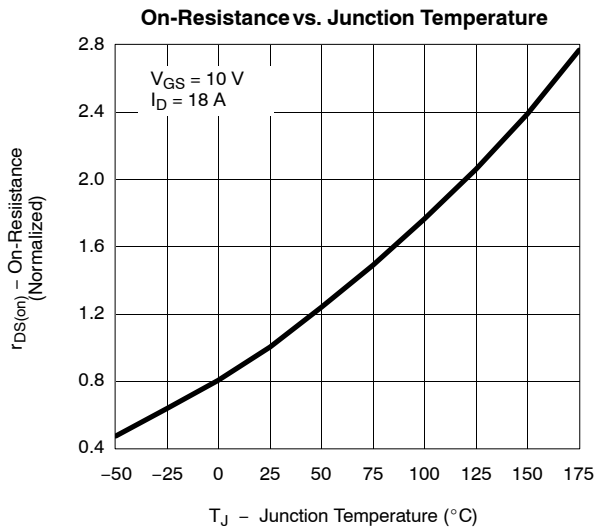
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



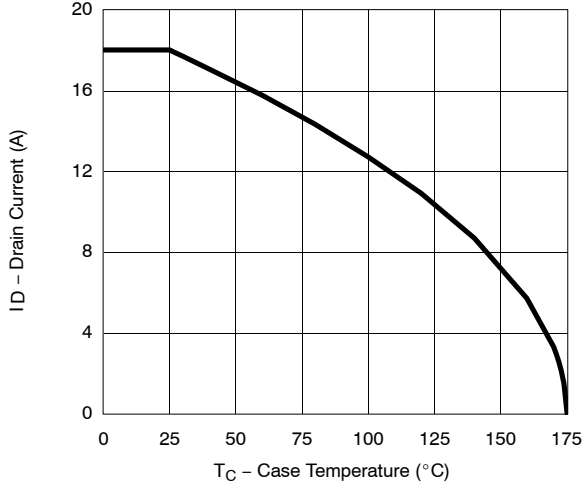
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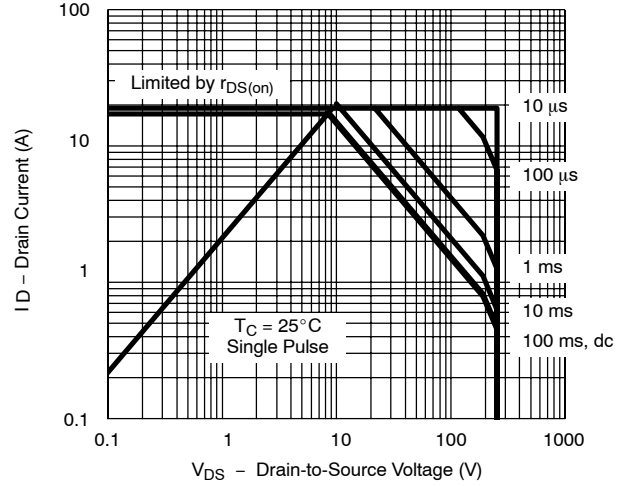


THERMAL RATINGS

Maximum Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

